

SOT-89-3L Plastic-Encapsulate Transistors

FEATURE

- High voltage
- Large continuous collector current capability
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:SOT-89-3L molded plastic
- Mounting position:any

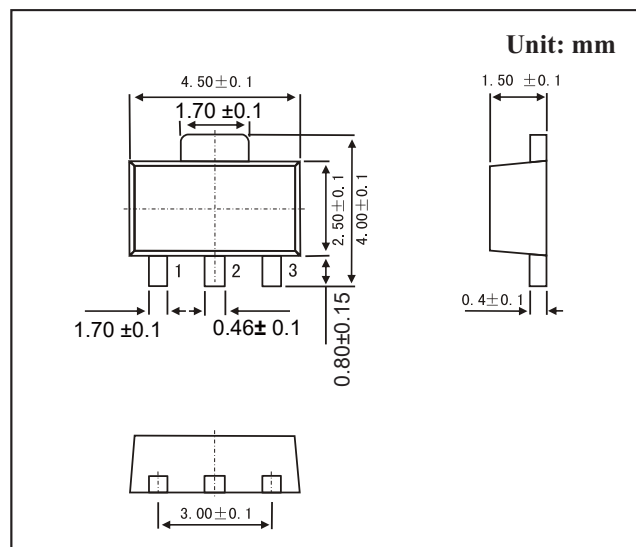
MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-160	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current -Continuous	I_C	-1	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 ~ +150	°C
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	250	°C/W

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}$, $I_E = 0$	-160		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}$, $I_B = 0$	-160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$, $I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -150\text{V}$, $I_E = 0$		-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{V}$, $I_C = 0$		-1	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -200\text{mA}$	60	320	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}$, $I_B = -50\text{mA}$		-1.5	V
Base-emitter voltage	V_{BE}	$I_C = -5\text{mA}$, $V_{CE} = -5\text{V}$		-0.75	V
Transition frequency	f_T	$V_{CE} = -5\text{V}$, $I_C = -200\text{mA}$	15		MHz



RATINGS AND CHARACTERISTIC CURVES

